

## Features

- 650 V, 40 A, Low Collector-Emitter Saturation Voltage ( $V_{CE(sat)}$ )
- Novel trench-gate field-stop technology
- Optimized for conduction
- Medium-speed switching
- Maximum operating  $T_j = 175\text{ }^\circ\text{C}$
- RoHS compliant\*

## Applications

- Switched-Mode Power Supplies (SMPS)
- Uninterruptible Power Sources (UPS)
- Power Factor Correction (PFC)
- Inverters
- Welding converters
- Photovoltaic

**BOURNS®**

## BIDW40N65ES5 Insulated Gate Bipolar Transistor (IGBT)

### General Information

The Bourns® Model BIDW40N65ES5 IGBT device combines technology from a MOS gate and a bipolar transistor, resulting in an optimum component for high voltage and high current applications. This device uses Trench-Gate Field-Stop technology providing greater control of dynamic characteristics while resulting in a lower Collector-Emitter Saturation Voltage ( $V_{CE(sat)}$ ) and fewer switching losses.

### Additional Information

Click these links for more information:



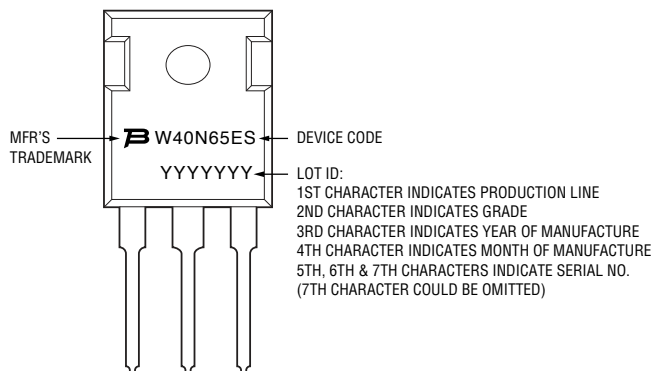
### Maximum Electrical Ratings ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CES}$	650	V
Continuous Collector Current ( $T_C = 25\text{ }^\circ\text{C}$ ), limited by $T_{jmax}$	$I_C$	80	A
Continuous Collector Current ( $T_C = 100\text{ }^\circ\text{C}$ ), limited by $T_{jmax}$	$I_C$	40	A
Pulsed Collector Current, $t_p$ limited by $T_{jmax}$	$I_{CP}$	160	A
Gate-Emitter Voltage	$V_{GE}$	$\pm 20$	V
Gate-Emitter Voltage ( $t_p \leq 10\text{ }\mu\text{s}$ , $D < 1\%$ )	$V_{GE}$	$\pm 30$	V
Continuous Forward Current ( $T_C = 100\text{ }^\circ\text{C}$ ), limited by $T_{jmax}$	$I_F$	40	A
Total Power Dissipation	$P_{total}$	230	W
Storage Temperature	$T_{STG}$	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature	$T_j$	-40 to +175	$^\circ\text{C}$

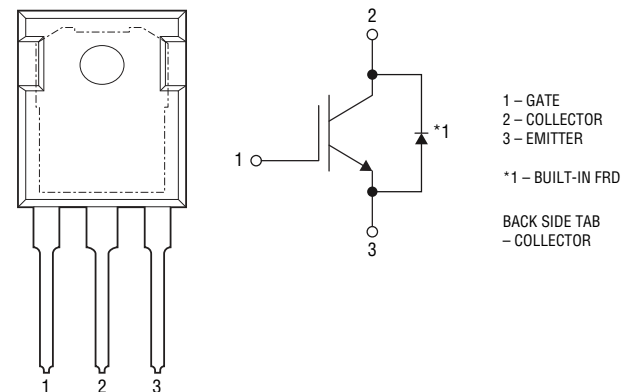
### Thermal Resistance

Parameter	Symbol	Max	Unit
IGBT Thermal Resistance Junction - Case	$R_{th(j-c)}_{IGBT}$	0.65	$^\circ\text{C/W}$
Diode Thermal Resistance Junction - Case	$R_{th(j-c)}_{Diode}$	0.6	$^\circ\text{C/W}$

### Typical Part Marking



### Internal Circuit



\*RoHS Directive 2015/863, Mar 31, 2015 and Annex. Specifications are subject to change without notice. Users should verify actual device performance in their specific applications. The products described herein and this document are subject to specific legal disclaimers as set forth on the last page of this document, and at [www.bourns.com/docs/legal/disclaimer.pdf](http://www.bourns.com/docs/legal/disclaimer.pdf).

# BIDW40N65ES5 Insulated Gate Bipolar Transistor (IGBT)

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## Static Electrical Characteristics ( $T_C = 25\text{ }^\circ\text{C}$ , Unless Otherwise Specified)

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Collector-Emitter Breakdown Voltage	$BV_{CES}$	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	650	—	—	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_C = 25\text{ }^\circ\text{C}$	—	1.35	1.7	V
		$V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_C = 150\text{ }^\circ\text{C}$	—	1.5	—	
Diode Forward On-Voltage	$V_F$	$I_F = 40\text{ A}, T_C = 25\text{ }^\circ\text{C}$	—	1.45	1.9	V
		$I_F = 40\text{ A}, T_C = 150\text{ }^\circ\text{C}$	—	1.32	—	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 250\text{ }\mu\text{A}$	3.2	4.5	5.8	V
Collector Cut-off Current	$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}$	—	—	100	$\mu\text{A}$
Gate-Emitter Leakage Current	$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$	—	—	$\pm 100$	nA

## Dynamic Electrical Characteristics ( $T_C = 25\text{ }^\circ\text{C}$ , Unless Otherwise Specified)

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Input Capacitance	$C_{ies}$	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	—	2856	—	pF
Output Capacitance	$C_{oes}$		—	82	—	
Reverse Transfer Capacitance	$C_{res}$		—	12	—	
Total Gate Charge	$Q_g$	$V_{CE} = 520\text{ V}, V_{GE} = 15\text{ V}, I_C = 40.0\text{ A}$	—	107	—	nC
Gate-Emitter Charge	$Q_{ge}$		—	24	—	
Gate-Collector Charge	$Q_{gc}$		—	31	—	

## IGBT Switching Characteristics (Inductive Load, $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise specified)

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Turn-on Delay Time	$t_{d(on)}$	$V_{CE} = 400\text{ V}, V_{GE} = 15\text{ V}, I_C = 40.0\text{ A}, R_G = 10\text{ }\Omega$	—	28	—	ns
Current Rise Time	$t_r$		—	26	—	ns
Turn-off Delay Time	$t_{d(off)}$		—	150	—	ns
Current Fall Time	$t_f$		—	36	—	ns
Turn-on Switching Energy	$E_{on}$		—	0.58	—	mJ
Turn-off Switching Energy	$E_{off}$		—	0.63	—	mJ
Total Switching Energy	$E_{ts}$		—	1.21	—	mJ

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# BIDW40N65ES5 Insulated Gate Bipolar Transistor (IGBT)

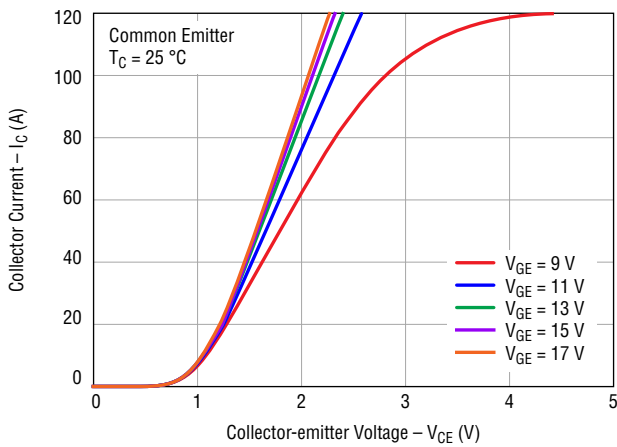


## Diode Switching Characteristics ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise specified)

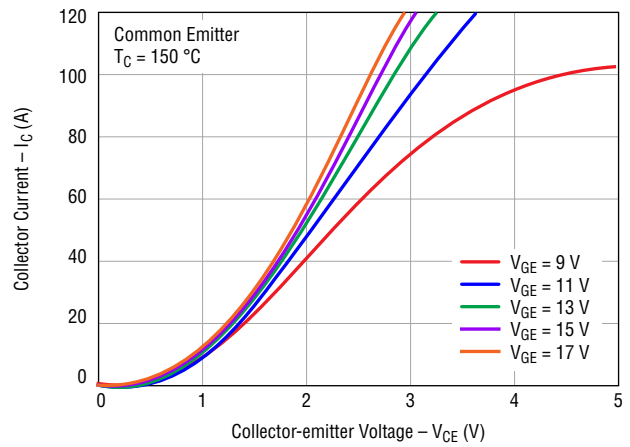
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Reverse Recovery Time	$t_{rr}$	$di_F/dt = 200\text{ A}/\mu\text{s}$ , $I_F = 40\text{ A}$	—	106	—	ns
Reverse Recovery Charge	$Q_{rr}$		—	258	—	nC

## Electrical Characteristic Performance

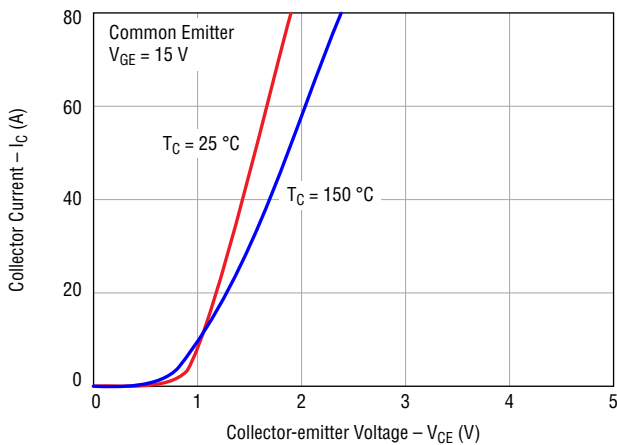
### Typical Output Characteristics



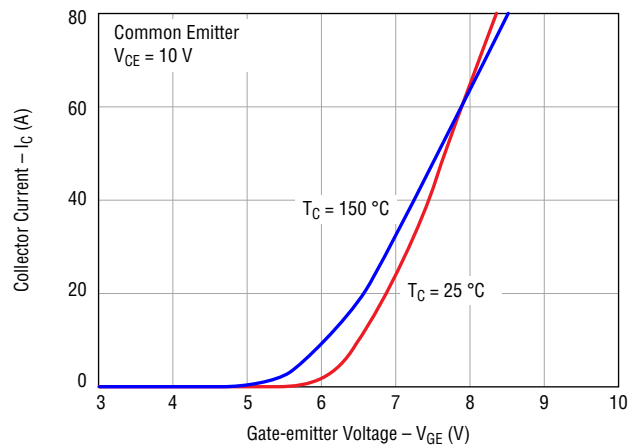
### Typical Output Characteristics



### Typical Saturation Voltage Characteristics



### Typical Transfer Characteristics



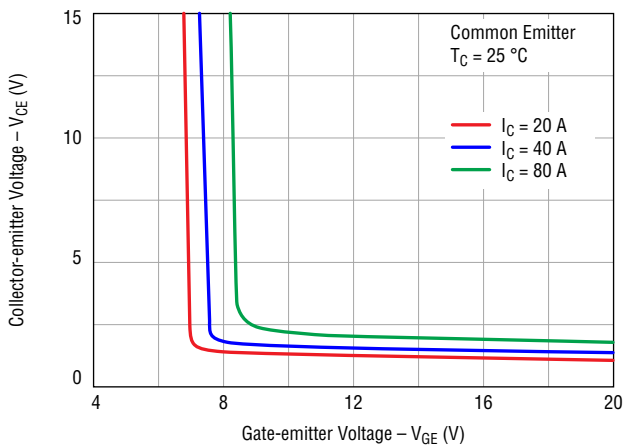
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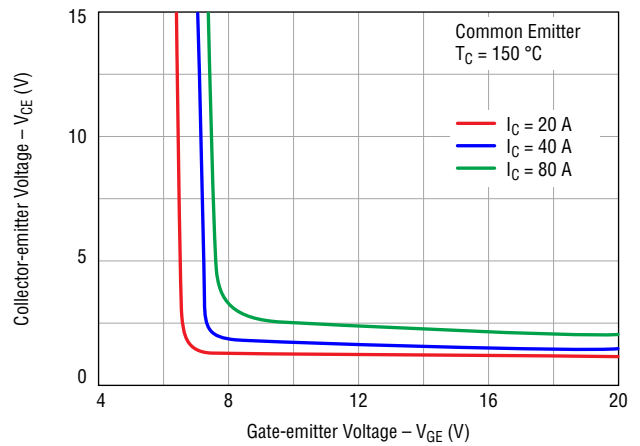
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## Electrical Characteristic Performance (continued)

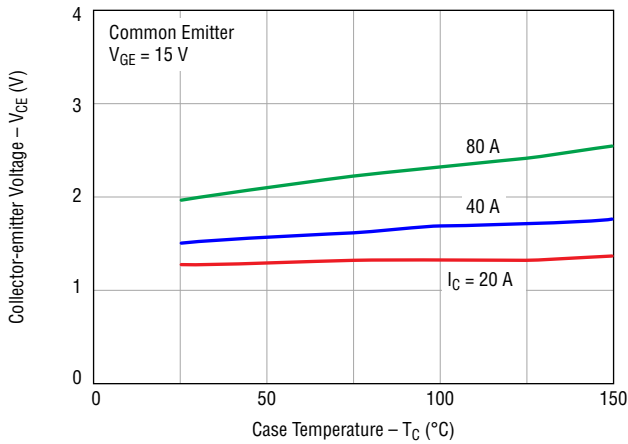
### Typical Saturation Voltage Drop vs $V_{GE}$ @ $T_C = 25\text{ }^\circ\text{C}$



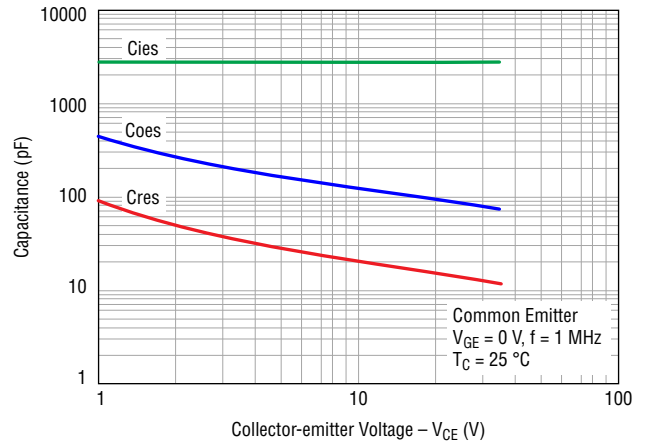
### Typical Saturation Voltage Drop vs $V_{GE}$ @ $T_C = 150\text{ }^\circ\text{C}$



### Typical Saturation Voltage Drop vs Temperature



### Typical Capacitance Characteristics



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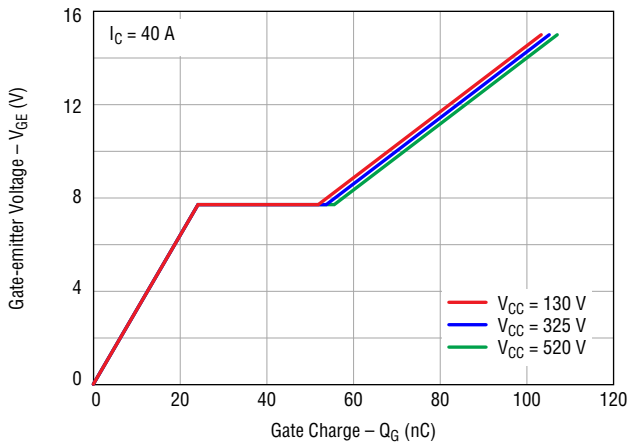
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# BIDW40N65ES5 Insulated Gate Bipolar Transistor (IGBT)

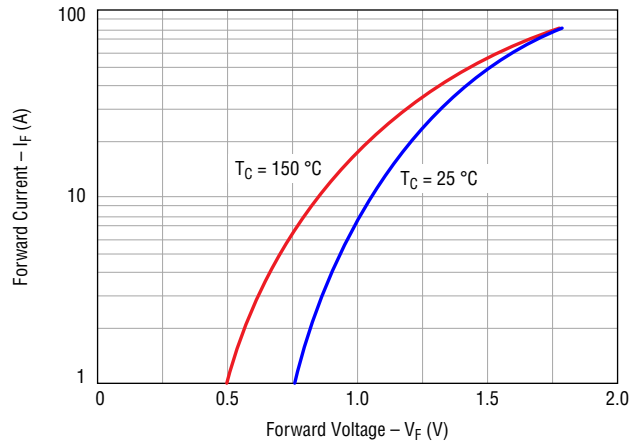


## Electrical Characteristic Performance (continued)

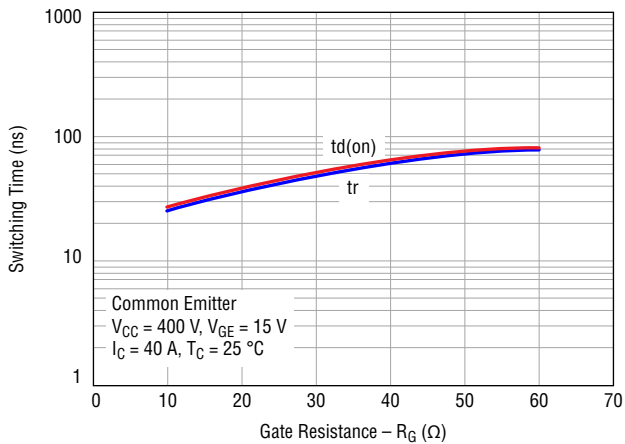
### Typical Gate Charge Characteristics



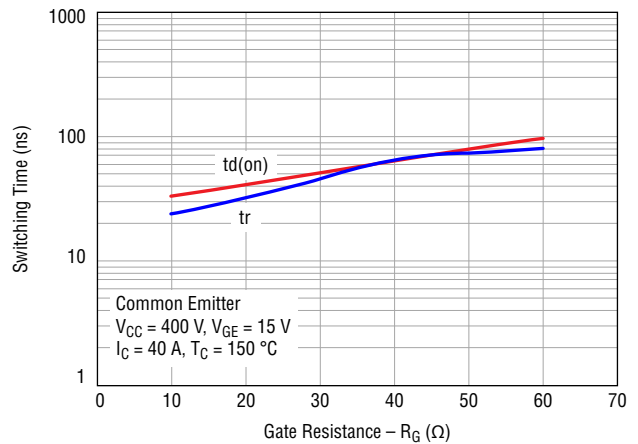
### Typical Forward Characteristics



### Typical Turn-on Characteristics vs Gate Resistance @ $T_C = 25$ °C



### Typical Turn-on Characteristics vs Gate Resistance @ $T_C = 150$ °C



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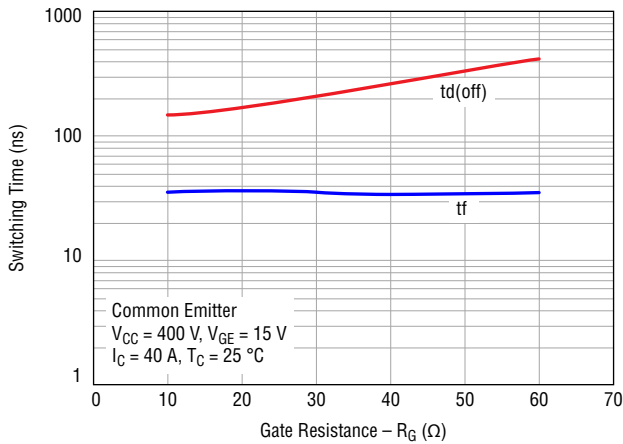
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# BIDW40N65ES5 Insulated Gate Bipolar Transistor (IGBT)

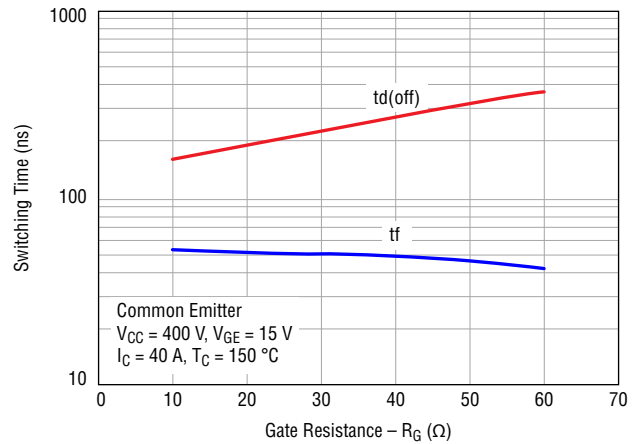


## Electrical Characteristic Performance (continued)

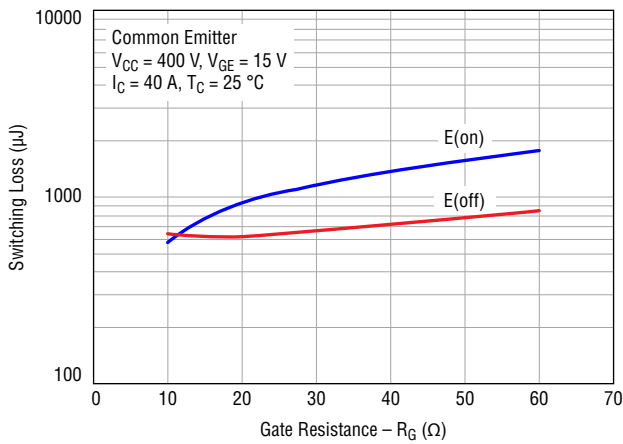
### Typical Turn-off Characteristics vs Gate Resistance @ $T_C = 25\text{ }^\circ\text{C}$



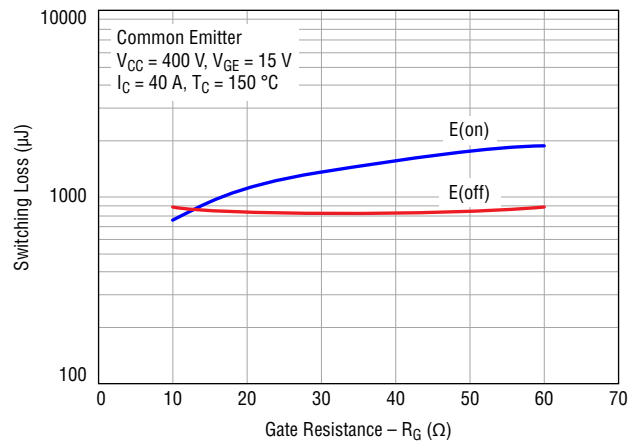
### Typical Turn-off Characteristics vs Gate Resistance @ $T_C = 150\text{ }^\circ\text{C}$



### Typical Switching Loss vs Gate Resistance @ $T_C = 25\text{ }^\circ\text{C}$



### Typical Switching Loss vs Gate Resistance @ $T_C = 150\text{ }^\circ\text{C}$



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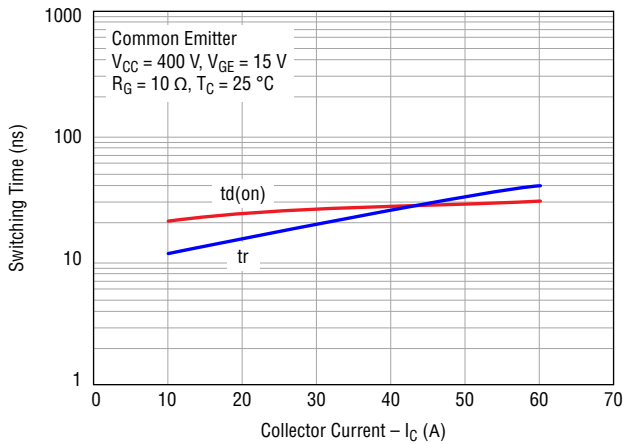
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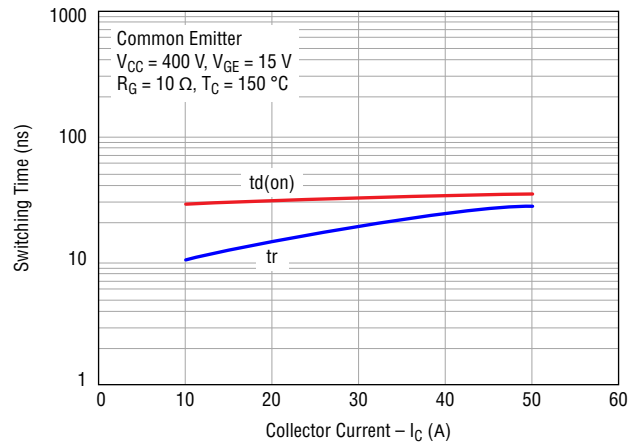


## Electrical Characteristic Performance (continued)

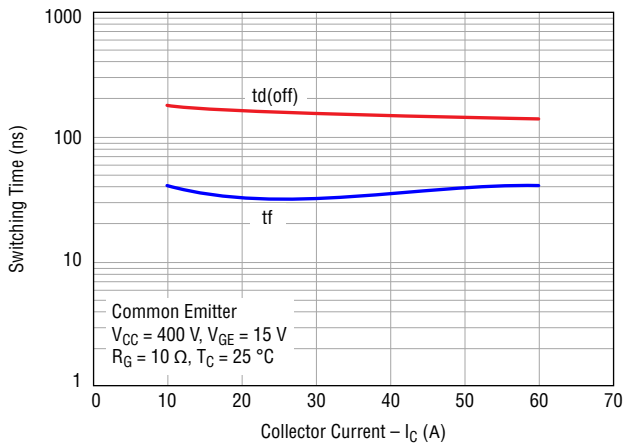
### Typical Turn-on Characteristics vs Collector Current @ $T_C = 25^\circ\text{C}$



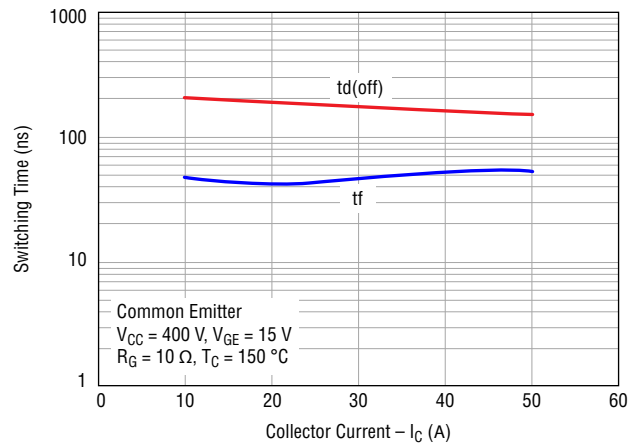
### Typical Turn-on Characteristics vs Collector Current @ $T_C = 150^\circ\text{C}$



### Typical Turn-off Characteristics vs Collector Current @ $T_C = 25^\circ\text{C}$



### Typical Turn-off Characteristics vs Collector Current @ $T_C = 150^\circ\text{C}$



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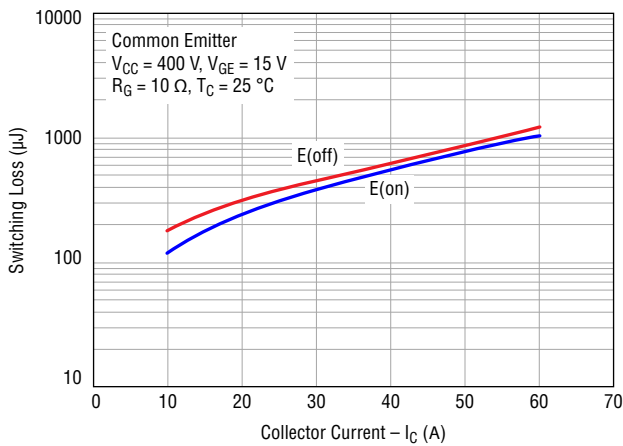
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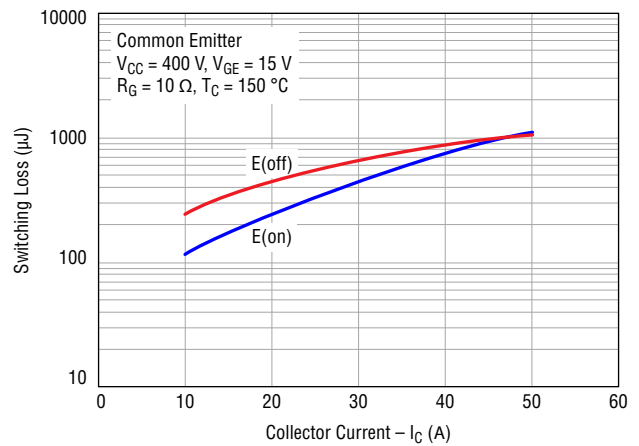


## Electrical Characteristic Performance (continued)

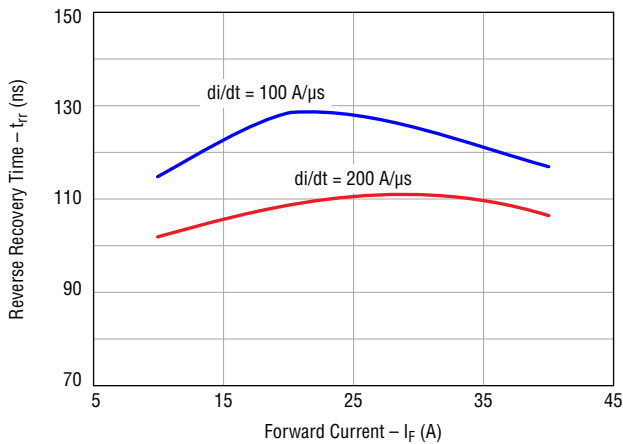
### Typical Switching Loss vs Collector Current @ $T_C = 25\text{ }^\circ\text{C}$



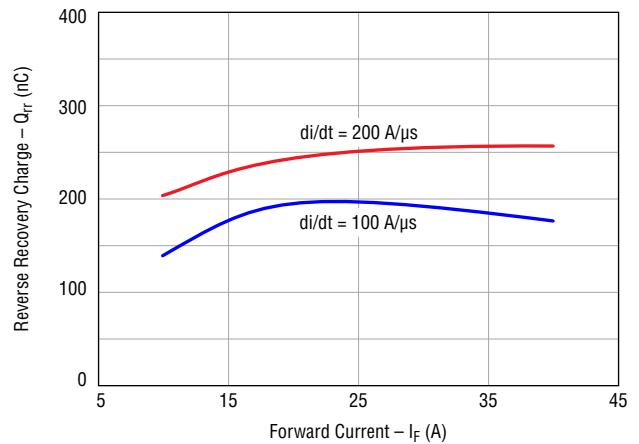
### Typical Switching Loss vs Collector Current @ $T_C = 150\text{ }^\circ\text{C}$



### Typical Reverse Recovery Time vs Forward Current



### Typical Reverse Recovery Charge vs Forward Current



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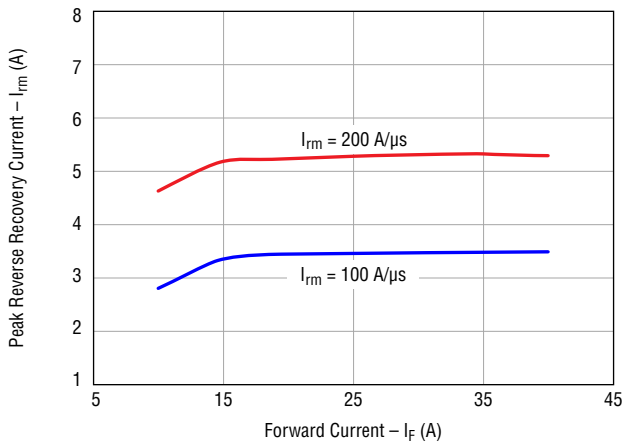
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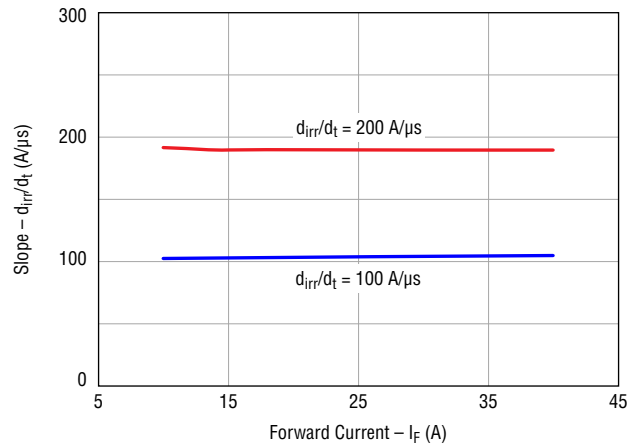


## Electrical Characteristic Performance (continued)

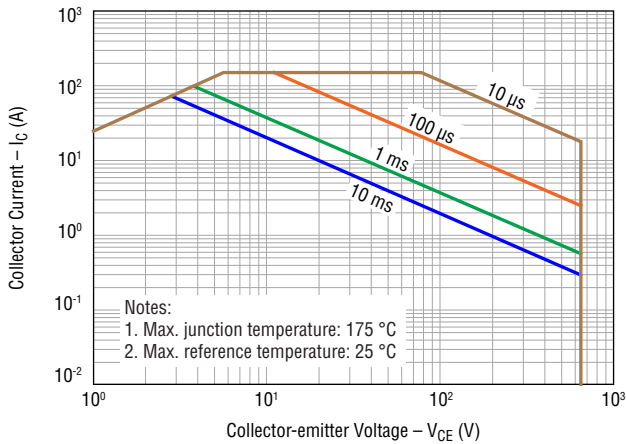
### Typical Peak Reverse Recovery Current vs Forward Current



### Typical Slope vs Forward Current



### Maximum Safe Operating Area



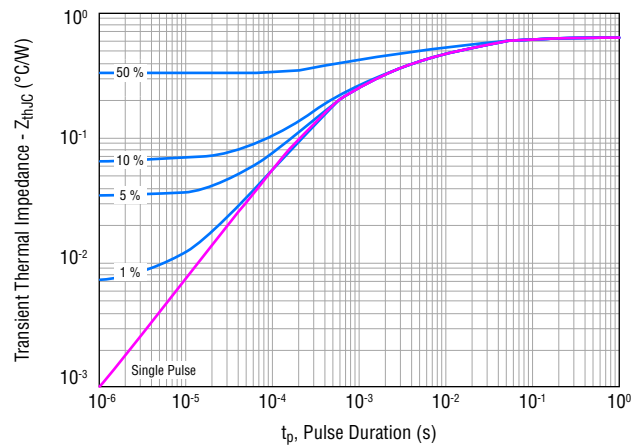
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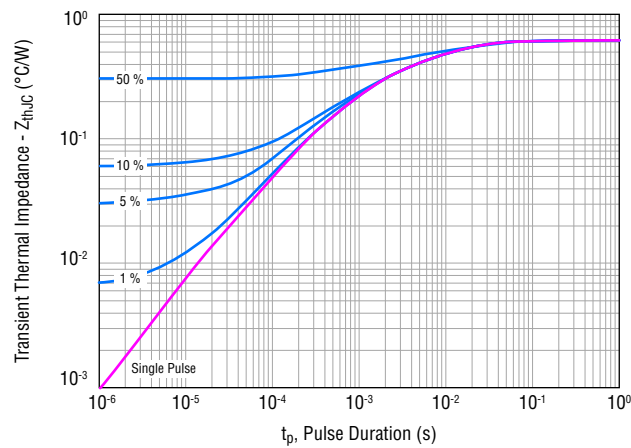
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## Electrical Characteristic Performance (continued)

### IGBT Transient Thermal Impedance vs $t_{p(on)}$ Duration ( $D=t_p/T$ )



### Diode Transient Thermal Impedance vs $t_{p(on)}$ Duration ( $D=t_p/T$ )



Specifications are subject to change without notice.

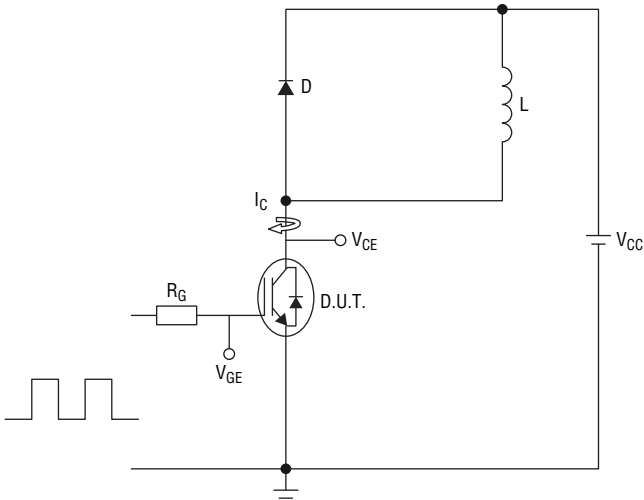
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# BIDW40N65ES5 Insulated Gate Bipolar Transistor (IGBT)



## Inductive Load Test Circuit



$L = 200 \mu\text{H}$ ,  $V_{CE} = 400 \text{ V}$ ,  $V_{GE} = 15 \text{ V}$ ,  $I_C = 40 \text{ A}$ ,  $R_G = 10 \Omega$

## How to Order

**B I D W 40 N 65 ES5**

B = Bourns® \_\_\_\_\_  
 I = IGBT \_\_\_\_\_  
 Type \_\_\_\_\_  
     D = Discrete  
 Package Code \_\_\_\_\_  
     W = TO-247-3L  
 Current Rating \_\_\_\_\_  
     40 = 40 A  
 Device Type \_\_\_\_\_  
     N = N-channel  
 Nominal Voltage (divided by 10) \_\_\_\_\_  
     65 = 650 V  
 Optimization \_\_\_\_\_  
     ES = Efficient Medium Speed  
 Version Number \_\_\_\_\_  
     5 = Revision Control

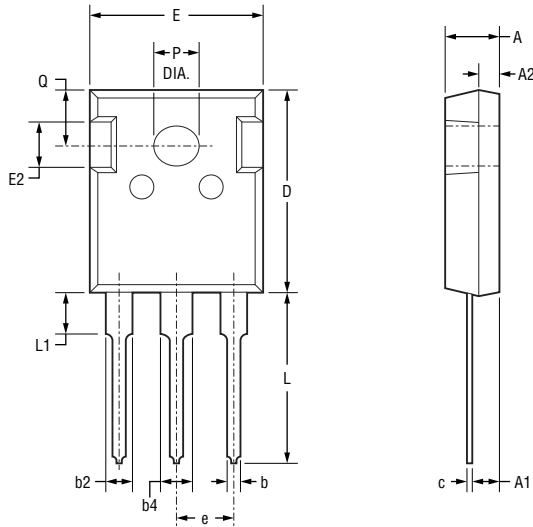
## Environmental Characteristics

ESD Class (HBM) .....2

# BIDW40N65ES5 Insulated Gate Bipolar Transistor (IGBT)



## Product Dimensions



DIMENSIONS:  $\frac{\text{MM}}{\text{(INCHES)}}$

Symbol	Min.	Nom.	Max.
A	$\frac{4.80}{(.189)}$	$\frac{5.00}{(.197)}$	$\frac{5.20}{(.205)}$
A1	$\frac{2.21}{(.087)}$	$\frac{2.41}{(.095)}$	$\frac{2.59}{(.102)}$
A2	$\frac{1.85}{(.073)}$	$\frac{2.00}{(.079)}$	$\frac{2.15}{(.085)}$
b	$\frac{1.11}{(.044)}$	—	$\frac{1.36}{(.054)}$
b2	$\frac{1.91}{(.075)}$	—	$\frac{2.25}{(.089)}$
b4	$\frac{2.91}{(.115)}$	—	$\frac{3.25}{(.128)}$
c	$\frac{0.51}{(.020)}$	—	$\frac{0.75}{(.030)}$
D	$\frac{20.80}{(.819)}$	$\frac{21.00}{(.827)}$	$\frac{21.30}{(.839)}$
E	$\frac{15.50}{(.610)}$	$\frac{15.80}{(.622)}$	$\frac{16.10}{(.634)}$
E2	$\frac{4.40}{(.173)}$	$\frac{5.00}{(.197)}$	$\frac{5.20}{(.205)}$
e	$\frac{5.44}{(.214)}$ BSC		
L	$\frac{19.72}{(.776)}$	$\frac{19.92}{(.784)}$	$\frac{20.22}{(.796)}$
L1	—	—	$\frac{4.30}{(.169)}$
P	$\frac{3.40}{(.134)}$	—	$\frac{3.80}{(.150)}$
Q	$\frac{5.60}{(.220)}$	$\frac{5.80}{(.228)}$	$\frac{6.00}{(.236)}$

## Packaging Specifications

BIDW40N65ES5..... 30 pieces per tube



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Email: [asiacus@bourns.com](mailto:asiacus@bourns.com)

EMEA: Tel: +36 88 885 877

Email: [eurocus@bourns.com](mailto:eurocus@bourns.com)

The Americas: Tel: +1-951 781-5500

Email: [americus@bourns.com](mailto:americus@bourns.com)

[www.bourns.com](http://www.bourns.com)

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